

FORMING TAPERED LOWER ELECTRODE PHASE-CHANGE MEMORIES

Abstract of the Disclosure

5 A phase-change memory may have a tapered lower
electrode coated with an insulator. The coated, tapered
electrode acts as a mask for a self-aligned trench etch to
electrically separate adjacent wordlines. In some
embodiments, the tapered lower electrode may be formed over
a plurality of doped regions, and isotropic etching may be
used to taper the electrode as well as part of the
10 underlying doped regions.